

15A 600V Fast recovery diode

1 Description

15A, 600V Ultrafast Diodes They have a low forward voltage drop and are of planar, silicon nitride passivated, ion-implanted, epitaxial construction. These devices are intended for use as energy—steering/clamping diodes and rectifiers in a variety of switching power supplies and other power switching—applications. Their low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor

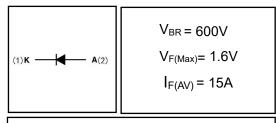
TO-220F provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink. TO-220F series comply with UL standards (File ref:E252906).

2 Features

- Low power loss,
- high efficiency Low forward voltage,
- high current capability High surge capacity
- Super fast recovery times
- high voltage

3 Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose





4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25 °C, unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage		V _{RRM}	600	V
Working Peak Reverse Voltage		V _{RWM}	600	V
DC Blocking Voltage		V _R	600	V
Average Rectified Forward Current	TO-220(Tc=135℃)	1	15	Α
Average Recilled Forward Current	TO-220F(Tc=100℃)	I _{F(AV)}	15	_ ^
Repetitive Peak Surge Current		I _{FRM}	30	Α
Nonrepetitive Peak Surge Current t=8.3ms		I _{FSM}	200	Α
Avalanche Energy L=1mH		E _{AS}	50	mJ
Operating Junction Temperature Range		Tj	- 55∼175	$^{\circ}$ C
Storage Temperature Range		T _{stg}	- 55∼175	$^{\circ}$

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE TO-220 TO-220F		UNIT
PARAWETER	STWIDOL			
Thermal Resistance, Junction to Case-sink	R _{thJC}	1.15	2.1	°C/W



4.3 Electrical Characteristics (Tc=25°C,unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
		I _F = 5A	-	1.05	-	V
		I _F = 10A	-	1.20	-	V
Maximum Instantaneous		I _F = 15A	-	1.33	1.60	V
Forward Voltage	V _F	I _F = 15A, T _C = 150°C	-	-	1.40	V
		I _F = 20A	-	1.42	1.65	V
		I _F = 30A		1.65		V
Maximum Instantaneous	I _R	V _R = 600V	-	-	1.0	uA
Reverse		V _R = 600V, T _a = 150°C	-	-	500	uA
Maximum Reverse	t _{rr}	V _R =30V IF=1A -dI/dt=50A/us	-	31	40	ns
Recovery Time						
Total capacitance	Ctot	V _R =0V f=1MHz	-	220	-	pF
DC Blocking Voltage	V_{BR}	I _R =100uA	610	650	-	V

DEFINITIONS

VF = Instantaneous forward voltage (pw = $300\mu s$, D = 2%).

IR = Instantaneous reverse current.

 $R\theta JC$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

5 Typical characteristics diagrams

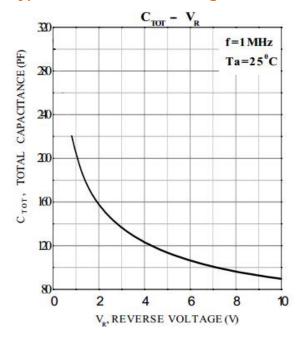


FIGURE 1. Total capacitance vs Voltage

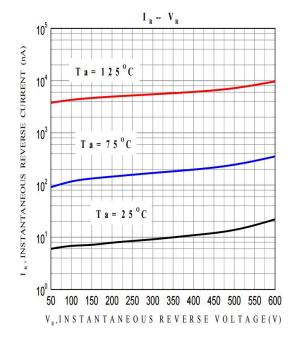
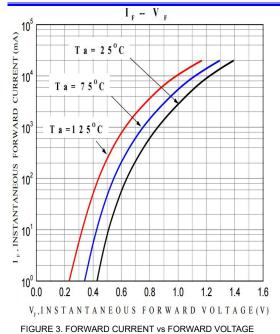


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE





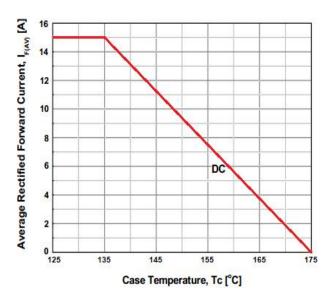


FIGURE 4. CURRENT DERATING CURVE

6 Typical Test Circuit and Waveform

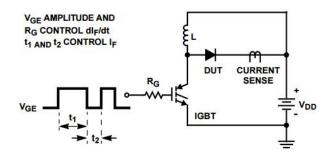


FIGURE 5. trr TEST CIRCUIT

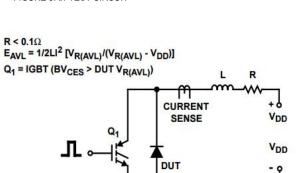


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT FIGURE

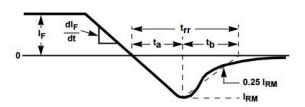


FIGURE 6. trr WAVEFORMS AND DEFINITIONS

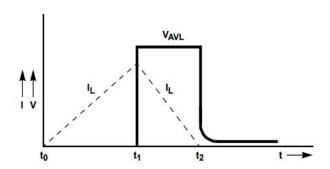
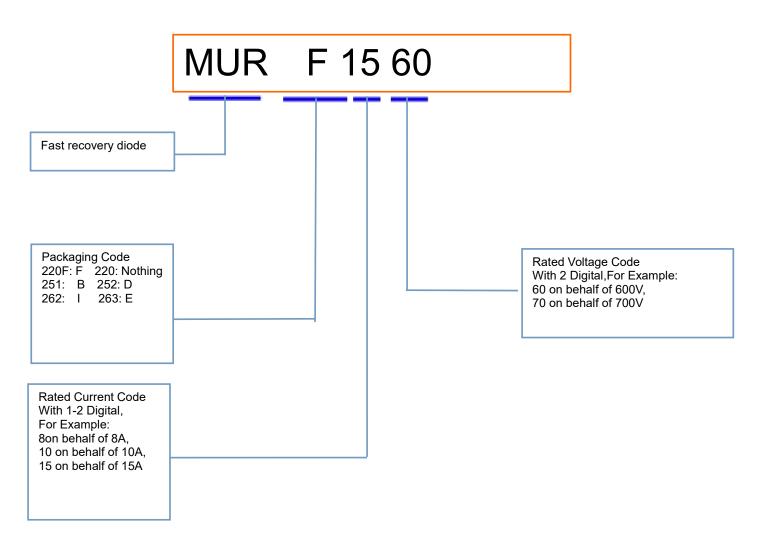


FIGURE8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS



7 Product Names Rules



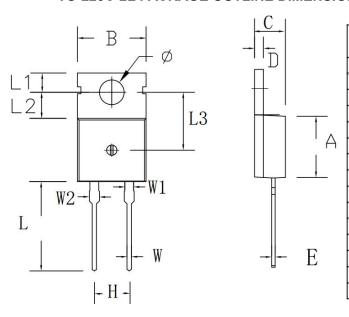
8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
MUR1560	TO-220C	MUR1560	Pb-free	Tube	1000/box
MURF1560	TO-220F	MURF1560	Pb-free	Tube	1000/box



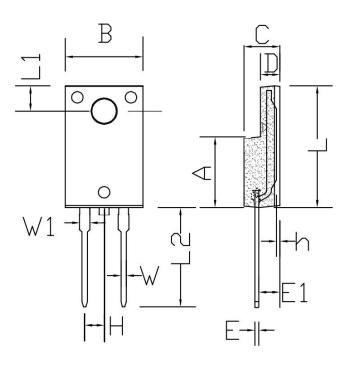
9 Dimensions

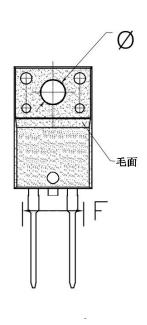
TO-220C-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions	In Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
A	8. 80	9. 30	0.346	0. 366
В	9. 70	10.30	0. 382	0.406
C	4. 25	4.75	0. 167	0. 187
D	1. 20	1. 45	0.047	0.057
Е	0. 40	0.60	0.016	0.024
Н	5.0	8 TYP	0. 201 TYP	
W	0.60	0.95	0.024	0.037
W1	1.05	1.45	0.041	0.057
W2	1. 20	1.60	0.047	0.063
L	12.60	13. 40	0. 496	0. 528
L1	2. 45	2. 95	0.096	0. 116
L2	3. 45	3. 95	0. 136	0. 156
L3	8. 15	8. 65	0. 321	0. 341
Φ	3. 50	3. 90	0. 138	0. 154

TO-220F-2L PACKAGE OUTLINE DIMENSIONS





Constant	DimensionsIn	Millimeters	
Symbol	min.	max.	
Α	7.90	8.50	
В	10.00	10.50	
С	4.30	4.90	
D	2.80	3.20	
L	14.80	15.30	
h	0.40	0.60	
L1	2.90	3.40	
L2	12.65	13.45	
W	0.60	0.80	
W1	1.15	1.55	
Н	2.54	TYP	
Е	0.60	0.70	
ф	2.90	3.40	
E1	2.40	2.90	
F	7.75	8.25	



10 Attentions

- Jiangsu Donghai Semiconductor Co.,Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Jiangsu Donghai Semiconductor Co.,Ltd. products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2017.03.31	1.0	Original	
2022.1.1	1.1	Modify company name	all
2022.7.15	1.2	Modify product DC parameters	1,2,3 page